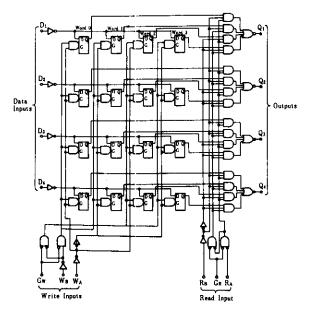
The HD74LS670, 16-bit register files incorporate the equivalent of 98 gates. The register file is organized as 4 words of 4 bits each and separate on-chip decoding is provided for addressing the the four word locations to either write-in or retrieve data.

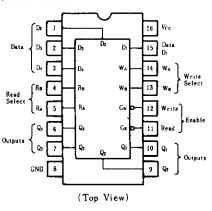
This permits simultaneous writing into one location and reading from another word location. Four data inputs are available which are used to supply the 4-bit word to be stored. Location of the word is determined by the write-address inputs A and B in conjunction with a write-enable signal. Data applied at the inputs should be in its true form. That is, if a high-level signal is desired from the output, a high-level is applied at the data input for that particular bit location. The latch inputs are arranged so that new data will be accepted only if both internal address gate inputs are high. When this condition exists, data at the D input is transferred to the latch output. When the write-enable input, Gw, is high, the data inputs are inhibited and their levels can cause no change in the information stored in the internal latches. When the read-enable input, GR, is high, the data outputs are inhibited and go into the highimpedance state. The individual address lines permit direct acquisition of data stored in any four of the latches. Four individual decoding gates are used to complete the address for reading a word.

When the read address is made in conjunction with the readenable signal, the word appears at the four outputs.

BLOCK DIAGRAM



■PIN ARRANGEMENT



EFUNCTION TABLE

W	rite Inpu	ts	Word					
Wв	WA	Gw	0	1	2	3		
L	L	L	Q-D	\mathbf{Q}_{o}	Q ₀	Q ₀		
L	н	L	Q ₀	Q-D	Q.	Q ₀		
Н	L	L	Q ₀	Q ₀	Q=D	Q,		
Н	Н	L	Q _o	Qo	Q ₀	Q-D		
×	×	Н	Q ₀	Q ₀	Q,	Q ₀		

F	lead Input	s	Outputs					
R _B	R₄	G _R	Qı	Q_2	Q ₃	Q,		
L	L	L	W 0 B1	W ₀ B ₂	W ₀ B ₃	W₀B₄		
L	Н	L	W ₁ B ₁	W ₁ B ₂	W ₁ B ₃	W ₁ B ₂		
H	L	L	W 2 B1	W ₂ B ₂	W 2 B3	W ₂ B ₄		
Н	Н	L	W 1 B1	W ₃ B ₂	W 3 B 3	W ₃ B		
×	×	Н	Z	Z	Z	Z		

Notes: H = high level, L = low level, X = irrelevant, Z = high impedance (off)

(Q=D) = The four selected internal flip-flop outputs will assume the states applied to the four external data inputs.

Q_e = The level of Q before the indicated input conditions were established.

 W_0B_1 = The first bit of word 0, etc.

PRECOMMENDED OPERATING CONDITIONS

1t	em	Symbol	min	typ	max	Unit
Supply voltage		V_{cc}	V _{CC} 4.75	5.00	5.25	v
		I_{OH}	_	-	-2.6	mА
Output curren	t	I_{oL}	_		8	mΑ
Pulse width	Read enable		25	_	-	
	Write enable	i i u	60		_	ns
	Data		10		_	
Setup time	Write enable	t.,,	15	-	-	ns
77 11	Data		15			
Hold time	Write enable	t,	5			ns
Latch time		tiesch	60	_	-	ns

MELECTRICAL CHARACTERISTICS $(Ta = -20 \sim +75^{\circ}C)$

Item	Symbol	Test Condi	tions	min	typ*	max	Unit
	V_{IH}			2.0	-		V
Input voltage	$V_{II.}$			_	-	0.8	V
	Von	Vcc-4.75V, ViH-2V, ViL-0.	8V, Ion = -2.6mA	2.4	_		V
Output voltage		$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V},$	Io1 - 4mA	_	_	0.4	v
	Vol	$V_{IL}=0.8V$	Io1 = 8mA	-	_	0.5	l v
0.00	I _{02H}	1/ f 053/ 1/ 03/	$V_o = 2.7 \text{V}$			20	μA
Off-state output current	IozL	$V_{CC} = 5.25 \text{V}, V_{IH} = 2 \text{V}$	Vo-0.4V		_	20	
	In Vcc*	$V_{CC} = 5.25 \text{V}, V_I = 2.7 \text{V}$	Any D, R or W			20	μΑ
			Gw	_		40	
			G_R		_	60	
		V _{cc} -5.25V, V _i -0.4V	Any D, R or W			-0.4	mA
Input current			Gw		_	-0.8	
			G_R			-1.2	
			Any D, R or W	-		0.1	mA
		$V_{CC} = 5.25 \text{V}, V_{I} = 7 \text{V}$	Gw		_	0.2	
			G _R	_		0.3	
Short-circuit output current	Ios	V_{cc} =5.25V		···30		-130	mΑ
Supply current	Icc**	Vcc-5.25V		_	30	50	mA
Input clamp voltage	V_{IX}	$V_{CC} = 4.75 \text{V}, I_{IN} = -18 \text{mA}$			_	-1.5	ν

^{*} V_{CC}=5V, Ta=25°C

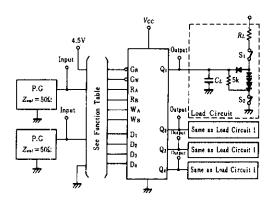
SWITCHING CHARACTERISTICS $(V_{CC}=5V, Ta=25^{\circ}C)$

Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
Propagation delay time	I P L H	Read	Qı~Qı	Q ₁ ~Q ₄	_	23	40	
	t _{PHL}	select				25	45	
	tpin	Write				26	45	
	t _{PHL}	enable	$Q_1 \sim Q_i$ $Q_1 \sim Q_i$	$Q_1 \sim Q_1$ $C_L = 15 \text{pF}$		28	50	
	tplH			$R_L = 2k\Omega$		25	45	
	t _{PHI}	Data		Q ₁ ~Q ₄			23	40
	t _{ZH}		<u> </u>		_	15	35	
Output enable time	tzi	Read			_	22	40	
Output disable time	tuz	enable	$Q_1 \sim Q_1$	C_L - 5pF,		30	50	
	tLZ			$R_L = 2k\Omega$		16	35	

^{**:} Maximum I_{CC} is guaranteed for the following worst case conditions: 4.5V is applied to all data inputs and both enable inputs, all address inputs are grounded and all outputs are open.

TESTING METHOD

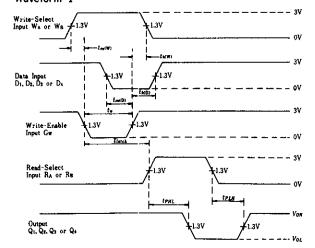
Test Circuit



Notes:

- 1. C_L includes probe and jig capacitance. 2. All diodes are 1S2074 B.

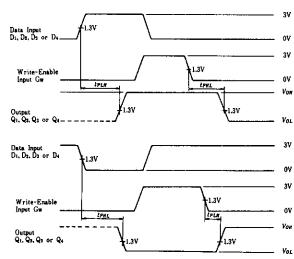
Waveform-1



Notes:

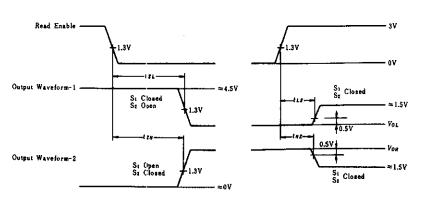
- 1. High-level input pulses at the select and data inputs are illustrated; however, times associated with low-level pulses are measured from the same reference points.
- 2. When measuring delay times from a read-select inputs, the read-enable input is low.
- 3. Input pulse; $t_{TLH} \le 15$ ns, $t_{THL} \le 6$ ns, PRR = 1MHz, duty cycle 50%

Waveform-2



Each select address is tested. Prior to the start of each of the Note: above test both write and read address inputs are stabilized with $W_A = R_A$ and $W_B = R_B$. During the test G_R is low.

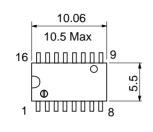
Waveform-3

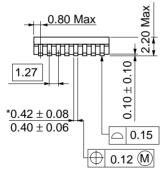


Waveform A is for an output with internal conditions such that the output is low except when disabled by the read-enable input. Waveform B is for an output with internal conditions such that the output is high except when disabled by the read-enable input.

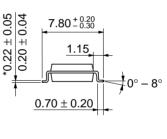
Unit: mm 19.20 20.00 Max 16 7.40 Max 6.30 1.3 1.11 Max 7.62 5.06 Max 2.54 Min 0.51 Min $0.25^{+0.13}_{-0.05}$ 0.48 ± 0.10 2.54 ± 0.25 $0^{\circ} - 15^{\circ}$ Hitachi Code DP-16 **JEDEC** Conforms EIAJ Conforms Weight (reference value) 1.07 g

Unit: mm





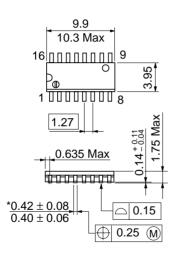


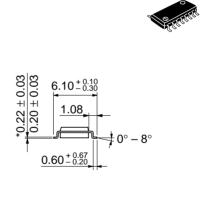


Hitachi Code	FP-16DA
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.24 g

*Dimension including the plating thickness
Base material dimension

Unit: mm





*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

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